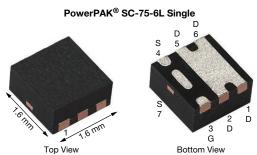


# N-Channel 100 V (D-S) MOSFET

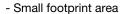


### Marking code: AJ

PRODUCT SUMMARY								
V <sub>DS</sub> (V)	100							
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.185							
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.310							
Q <sub>g</sub> typ. (nC)	1.8							
I <sub>D</sub> (A) <sup>a</sup>	6.3							
Configuration	Single							

#### **FEATURES**

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-75 package



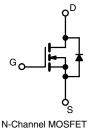
- Low on-resistance
- 100 % R<sub>a</sub> and UIS tested
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

### **APPLICATIONS**

- DC/DC converters
- Full-bridge converters
- For power bricks and POL power



ROHS COMPLIANT HALOGEN FREE



ORDERING INFORMATION	
Package	PowerPAK SC-75
Lead (Pb)-free and halogen-free	SiB456DK-T1-GE3

ABSOLUTE MAXIMUM RATINGS (	T <sub>A</sub> = 25 °C, unless	s otherwise note	ed)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	100	V
Gate-source voltage		V <sub>GS</sub>	± 20	v
	T <sub>C</sub> = 25 °C		6.3	
Continuous drain current (T = 150 °C)	T <sub>C</sub> = 70 °C	Ι , Γ	5	
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>A</sub> = 25 °C	I <sub>D</sub>	2.7 b, c	
	T <sub>A</sub> = 70 °C		2.2 b, c	A
Pulsed drain current (t = 300 μs)		I <sub>DM</sub>	7	A
Casting and a superior disable account	T <sub>C</sub> = 25 °C		6.3	
Continuous source-drain diode current	T <sub>A</sub> = 25 °C	l <sub>S</sub>	2 <sup>b, c</sup>	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	2.4	
Single pulse avalanche energy	L = 0.1 IIII	E <sub>AS</sub>	0.29	mJ
	T <sub>C</sub> = 25 °C		13	
Manipular de la compania del compania del compania de la compania del compania del compania de la compania del compania de	T <sub>C</sub> = 70 °C		8.4	w
Maximum power dissipation	T <sub>A</sub> = 25 °C	P <sub>D</sub>	2.4 b, c	VV
	T <sub>A</sub> = 70 °C		1.6 <sup>b, c</sup>	
Operating junction and storage temperature range	ge	т т	-55 to +150	°C
Soldering recommendations (peak temperature)	d, e	T <sub>J</sub> , T <sub>stg</sub>	260	

THERMAL RESISTANCE RATINGS									
PARAMETER		SYMBOL	TYPICAL	MAXIMUM	UNIT				
Maximum junction-to-ambient b, f	t ≤ 5 s	R <sub>thJA</sub>	41	51	°C/M				
Maximum junction-to-case (drain)	Steady state	$R_{thJC}$	7.5	9.5	°C/W				

#### **Notes**

- a.  $T_C = 25$  °C
- b. Surface mounted on 1" x 1" FR4 board
- c. t = 5 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-75 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- f. Maximum under steady state conditions is 105 °C/W



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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	100	-	-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	L 050A	-	54	-	\//00
V <sub>GS(th)</sub> temperature coefficient	$\Delta V_{GS(th)}/T_J$	I <sub>D</sub> = 250 μA	-	-4.1	-	mV/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.6	-	3	V
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zoro goto voltago droip ourrent		V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	10	μA
On-state drain current a	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	6	-	-	Α
Drain actives on state resistance ?		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.9 A	-	0.153	0.185	0
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 1.5 \text{ A}$	-	0.220	0.310	Ω
Forward transconductance a	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.9 A	-	3.7	-	S
Dynamic <sup>b</sup>						
Input capacitance	C <sub>iss</sub>		-	130	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	-	54	-	pF
Reverse transfer capacitance	C <sub>rss</sub>		-	10	-	
Talal and a discuss	0	$V_{DS} = 50 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 2.7 \text{ A}$	-	3.3	5	nC
Total gate charge	Qg		-	1.8	2.7	
Gate-source charge	Q <sub>gs</sub>	$V_{DS} = 50 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 2.7 \text{ A}$	-	0.7	-	
Gate-drain charge	Q <sub>gd</sub>		-	1	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz	1.3	6.5	13	Ω
Turn-on delay time	t <sub>d(on)</sub>		-	15	30	
Rise time	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 23 \Omega$	-	45	90	
Turn-off delay time	t <sub>d(off)</sub>	$I_D\cong 2.2~A,~V_{GEN}=4.5~V,~R_g=1~\Omega$	-	11	20	
Fall time	t <sub>f</sub>		-	13	25	
Turn-on delay time	t <sub>d(on)</sub>		-	5	10	ns
Rise time	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, \text{ R}_{L} = 23 \Omega$	-	11	20	
Turn-off delay time	t <sub>d(off)</sub>	$I_D\cong 2.2$ A, $V_{GEN}$ = 10 V, $R_g$ = 1 $\Omega$	-	10	20	=
Fall time	t <sub>f</sub>		-	10	20	
<b>Drain-Source Body Diode Characteris</b>	tics					
Continuous source-drain diode current	Is	T <sub>C</sub> = 25 °C	-	-	6.3	
Pulse diode forward current	I <sub>SM</sub>		-	-	7	A
Body diode voltage	V <sub>SD</sub>	$I_S = 2.2 \text{ A}, V_{GS} = 0 \text{ V}$	-	0.9	1.2	V
Body diode reverse recovery time	t <sub>rr</sub>		-	25	50	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$I_F = 2.2 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s},$	-	20	40	nC
Reverse recovery fall time	t <sub>a</sub>	$T_{J} = 25  ^{\circ}\text{C}$	-	18	-	ns
Reverse recovery rise time	t <sub>b</sub>		-	7	-	

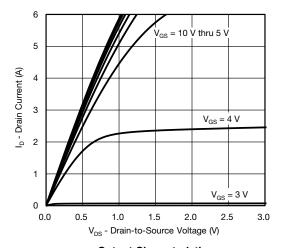
#### Notes

- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing

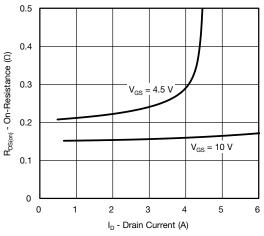
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



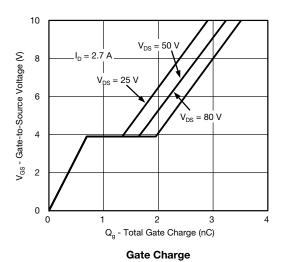
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

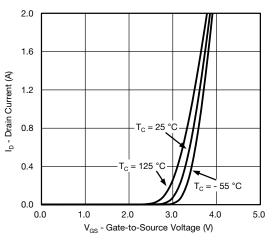


### **Output Characteristics**

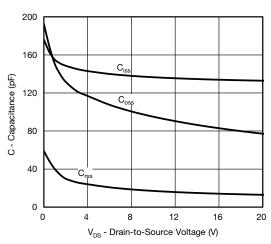


On-Resistance vs. Drain Current and Gate Voltage

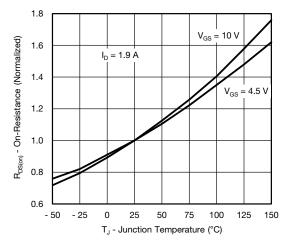




**Transfer Characteristics** 



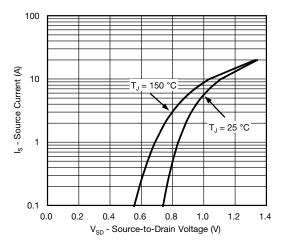
Capacitance



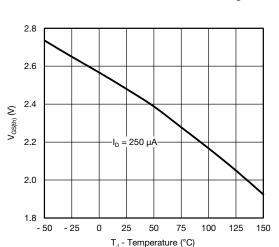
On-Resistance vs. Junction Temperature



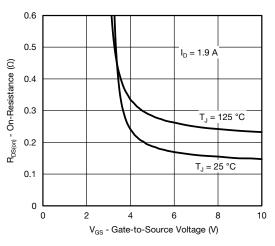
# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



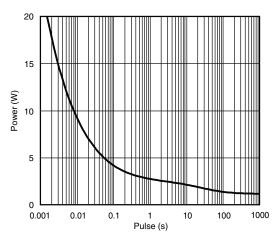
#### Source-Drain Diode Forward Voltage



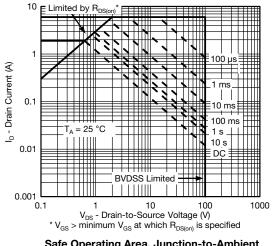
**Threshold Voltage** 



On-Resistance vs. Gate-to-Source Voltage



Single Pulse Power, Junction-to-Ambient



Safe Operating Area, Junction-to-Ambient

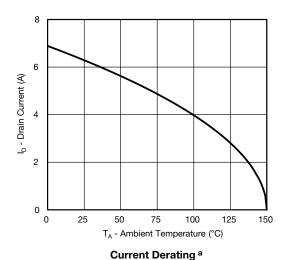
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

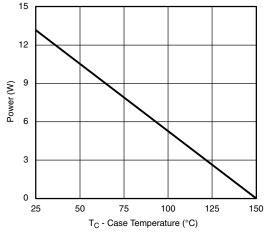




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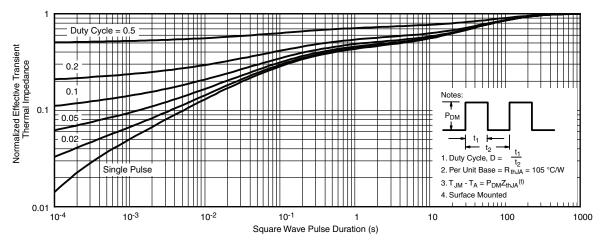
#### **Power Derating**

#### Note

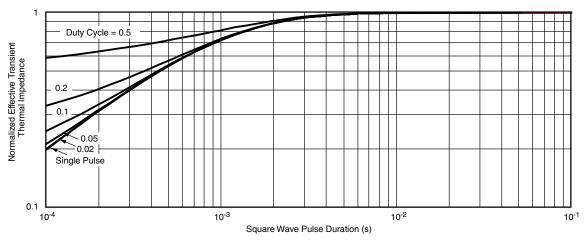
a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



# TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



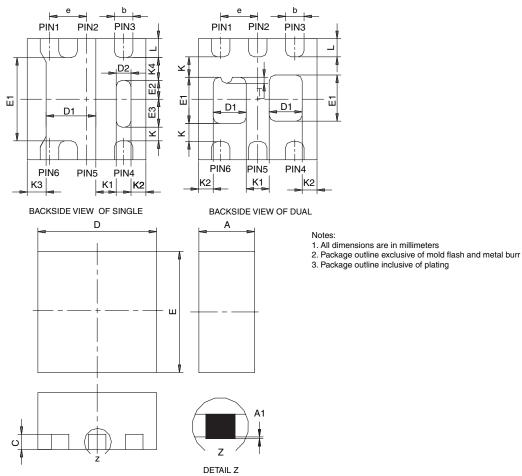
Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?62715">www.vishay.com/ppg?62715</a>.



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# PowerPAK® SC75-6L



	SINGLE PAD						DUAL PAD						
DIM	M	ILLIMETER	RS		INCHES		M	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032	
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002	
b	0.18	0.25	0.33	0.007	0.010	0.013	0.18	0.25	0.33	0.007	0.010	0.013	
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010	
D	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
D1	0.57	0.67	0.77	0.022	0.026	0.030	0.34	0.44	0.54	0.013	0.017	0.021	
D2	0.10	0.20	0.30	0.004	0.008	0.012							
Е	1.53	1.60	1.70	0.060	0.063	0.067	1.53	1.60	1.70	0.060	0.063	0.067	
E1	1.00	1.10	1.20	0.039	0.043	0.047	0.51	0.61	0.71	0.020	0.024	0.028	
E2	0.20	0.25	0.30	0.008	0.010	0.012							
E3	0.32	0.37	0.42	0.013	0.015	0.017							
е		0.50 BSC			0.020 BSC	;	0.50 BSC			0.020 BSC			
K		0.180 TYP	)		0.007 TYP	ı	0.245 TYP			0.010 TYP			
K1		0.275 TYP	)		0.011 TYP			0.320 TYP			0.013 TYP		
K2		0.200 TYP	)	0.008 TYP			0.200 BSC			0.008 TYP			
К3		0.255 TYP	)	0.010 TYP									
K4		0.300 TYP	1		0.012 TYP								
L	0.15	0.25	0.35	0.006	0.010	0.014	0.15	0.25	0.35	0.006	0.010	0.014	
Т							0.03	0.08	0.13	0.001	0.003	0.005	
ECN: C-07431 Rev C 06-Aug-07													

ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5935

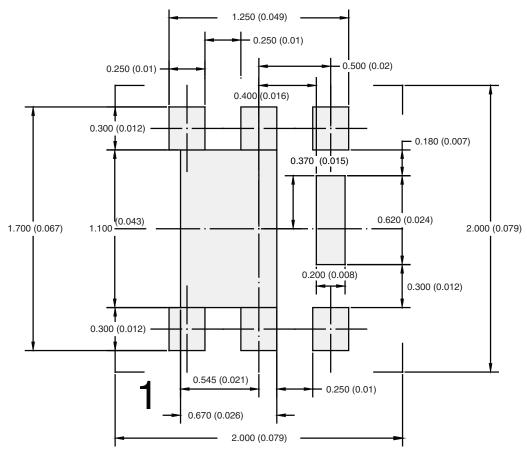
Document Number: 73000

06-Aug-07

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# RECOMMENDED PAD LAYOUT FOR PowerPAK® SC75-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOTE

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